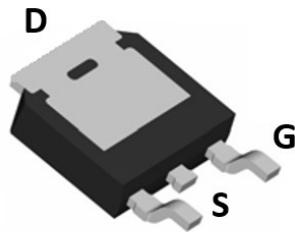
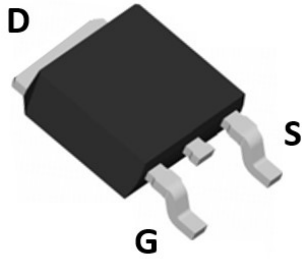
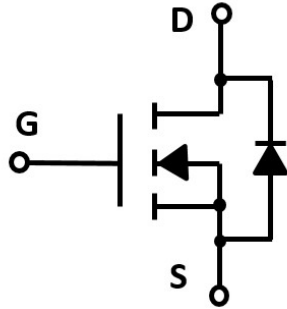


## N-Channel Enhancement Mode Field Effect Transistor



**TO-252**



### Product Summary

- $V_{DS}$  60 V
- $I_D$  90 A
- $R_{DS(ON)}$  ( at  $V_{GS}=10V$ ) <7.2 mohm
- $R_{DS(ON)}$  ( at  $V_{GS}=4.5V$ ) <8.5 mohm
- 100% UIS Tested
- 100%  $\nabla V_{DS}$  Tested

### General Description

- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low  $R_{DS(ON)}$

### Applications

- DC-DC Converters
- Power management functions
- Motor Drive applications

### ■ Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	60	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_C=25^\circ\text{C}$	$I_D$	90	A
	$T_C=100^\circ\text{C}$		57	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	300	A
Total Power Dissipation @ $T_C=25^\circ\text{C}$ <sup>B</sup>		$P_D$	110	W
Total Power Dissipation @ $T_C=100^\circ\text{C}$ <sup>B</sup>		$P_D$	44	W
Total Power Dissipation @ $T_A=25^\circ\text{C}$ <sup>C</sup>		$P_D$	6.2	W
Single Pulse Avalanche Energy <sup>D</sup>		$E_{AS}$	196	mJ
Thermal Resistance Junction-to-Case		$R_{\theta JC}$	1.14	$^\circ\text{C}/\text{W}$
Thermal Resistance Junction-to-Ambient		$R_{\theta JA}$	20	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~+150	$^\circ\text{C}$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJD90N06A	F2	YJD90N06A	2500	/	25000	13" reel



# YJD90N06A

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.5	2.5	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> =15A		5.6	7.2	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> =10A		6.8	8.5	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =15A, V <sub>GS</sub> =0V		0.80	1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				90	A
Gate resistance	R <sub>g</sub>	f=1 MHz, Open drain		2.1		Ω
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHZ		5170		pF
Output Capacitance	C <sub>oss</sub>			300		
Reverse Transfer Capacitance	C <sub>rss</sub>			155		
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub> (10V)	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, I <sub>D</sub> =20A		102		nC
Total Gate Charge	Q <sub>g</sub> (4.5V)			48		
Gate-Source Charge	Q <sub>gs</sub>			18.7		
Gate-Drain Charge	Q <sub>gd</sub>			20		
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =20A, di/dt=100A/us		18		nC
Reverse Recovery Time	t <sub>rr</sub>			27		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =30V, I <sub>D</sub> =20A R <sub>GEN</sub> =3Ω		12		ns
Turn-on Rise Time	t <sub>r</sub>			46		
Turn-off Delay Time	t <sub>D(off)</sub>			90		
Turn-off fall Time	t <sub>f</sub>			80		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. The value of R<sub>θJA</sub> is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C.

D. T<sub>J</sub>=25°C, V<sub>DD</sub>=55V, V<sub>G</sub>=10V, L=0.5mH.



## ■ Typical Performance Characteristics

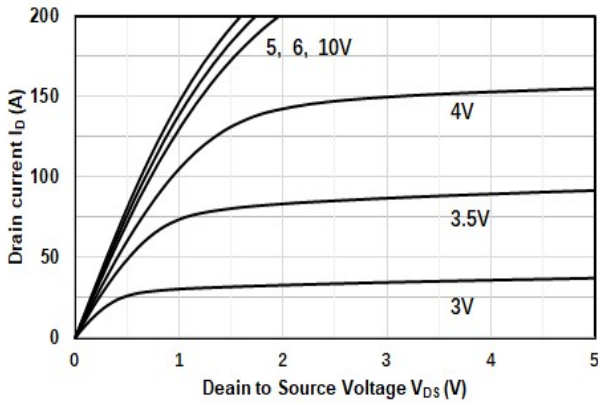


Figure1. Output Characteristics

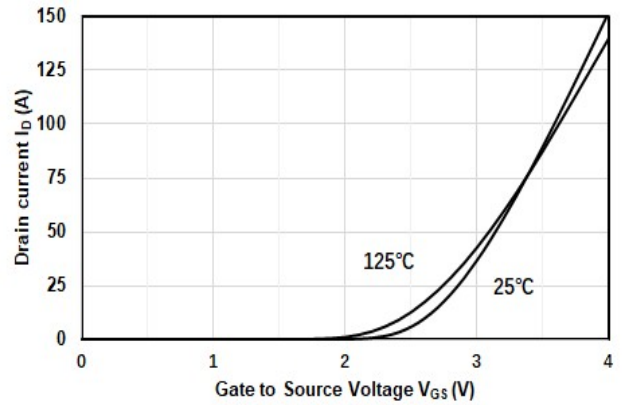


Figure2. Transfer Characteristics

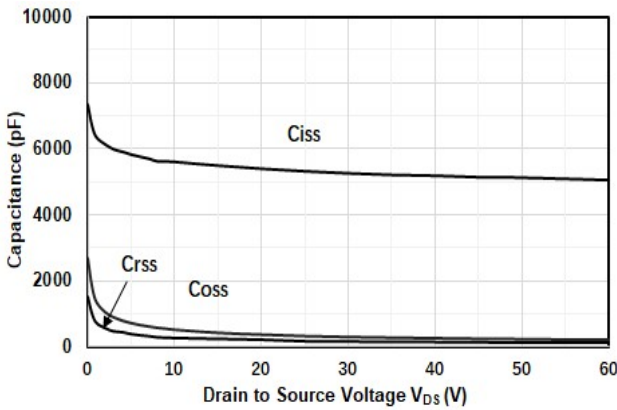


Figure3. Capacitance Characteristics

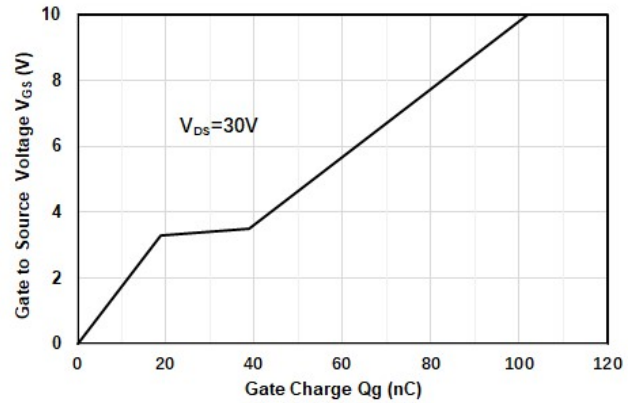


Figure4. Gate Charge

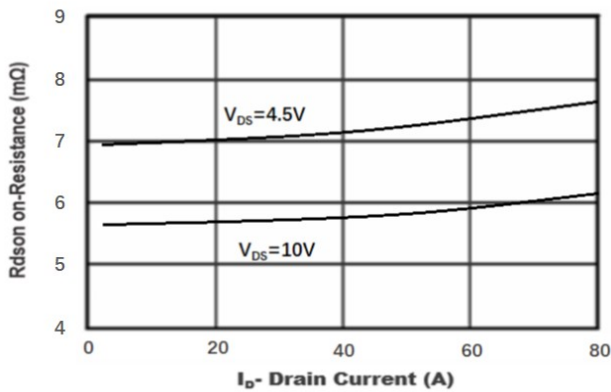


Figure5. Drain-Source on Resistance

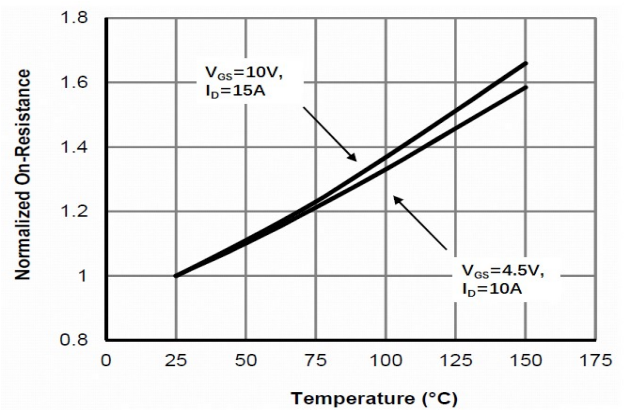


Figure6. Drain-Source on Resistance



# YJD90N06A

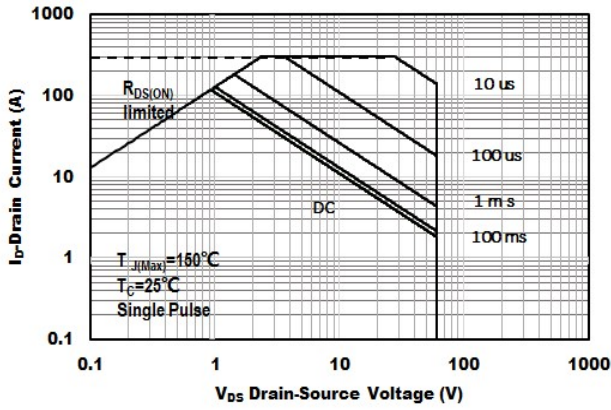


Figure7. Safe Operation Area

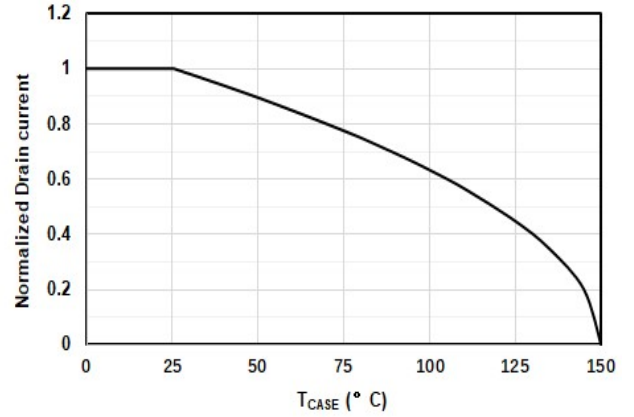


Figure8. Drain current vs. Case Temperature

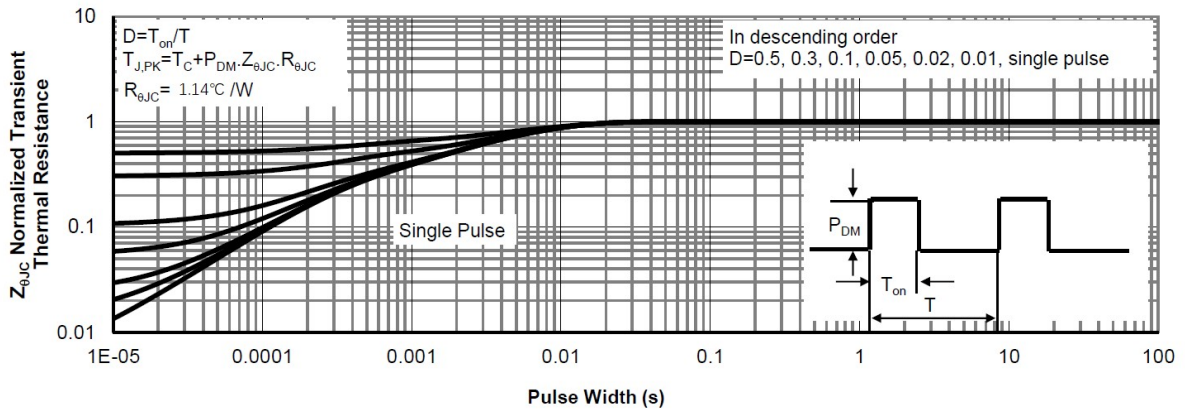
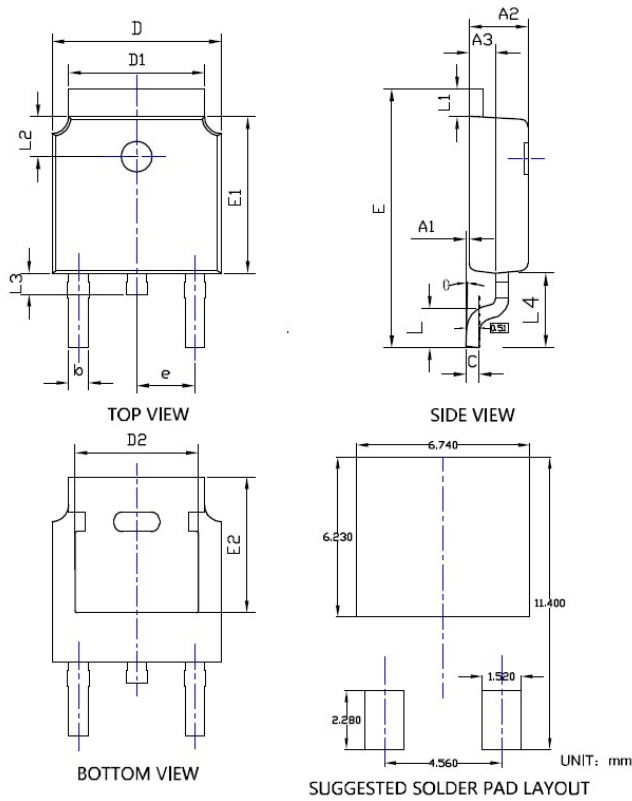


Figure9. Normalized Maximum Transient Thermal Impedance



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## ■TO-252 Package Information



SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.008	0.000	---	0.200
A2	0.087	0.091	0.094	2.200	2.300	2.400
A3	0.035	0.039	0.043	0.900	1.000	1.100
b	0.026	0.030	0.034	0.660	0.760	0.860
c	0.018	0.020	0.023	0.460	0.520	0.580
D	0.256	0.260	0.264	6.500	6.600	6.700
D1	0.203	0.209	0.215	5.150	5.300	5.450
D2	0.181	0.189	0.195	4.600	4.800	4.950
E	0.390	0.398	0.406	9.900	10.100	10.300
E1	0.236	0.240	0.244	6.000	6.100	6.200
E2	0.203	0.209	0.215	5.150	5.300	5.450
e	0.090BSC			2.286BSC		
L	0.049	0.059	0.069	1.250	1.500	1.750
L1	0.035	---	0.050	0.900	---	1.270
L2	0.055	---	0.075	1.400	---	1.900
L3	0.240	0.310	0.039	0.600	0.800	1.000
L4	0.114REF			2.900REF		
⊖	0*	---	10*	0*	---	10*

NOTE:  
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.  
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.  
 3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



## YJD90N06A

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